

Isc N-Channel MOSFET Transistor

IRF540NL

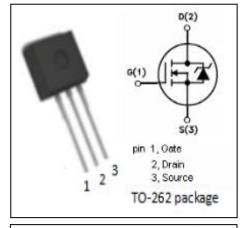
• FEATURES

- With To-262 package
- · Low input capacitance and gate charge
- · Low gate input resistance
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Switching applications





| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|----------|---------------|--|
| V _{DSS} | Drain-Source Voltage | 100 | V | |
| V _{GSS} | Gate-Source Voltage | ±20 | V | |
| l _D | Drain Current-ContinuousTc=25℃ Tc=100℃ | 33 23 | А | |
| I _{DM} | Drain Current-Single Pulsed | 110 | А | |
| P_D | Total Dissipation @T _c =25°C | 130 | W | |
| T _{ch} | Max. Operating Junction Temperature | 175 | ${\mathbb C}$ | |
| T _{stg} | Storage Temperature | -55~175 | ${\mathbb C}$ | |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|-----------|------------------------------------|------|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 1.15 | °C/W |

| G = G = D2 | 13 | 42 | | , p |
|------------|-----|---------------|-------|-----|
| | | mm | | |
| | DIM | MIN | MAX | |
| | A | 4.37 | 4.77 | |
| | A1 | 1.22 | 1.42 | |
| | A2 | 2.47 | 2.87 | |
| | Ъ | 0.70 | 0.97 | |
| | Ъ2 | 1.17 | 1.42 | |
| | С | 0.28 | 0.53 | |
| | D | 23.20 | 24.02 | |
| | D1 | 8.38 | 8.90 | |
| | D2 | 6.00 | -8 | |
| | E | 9.90 | 10.39 | |
| | E4 | 7.30 | _ | |
| | е | 2.54BSC | | |
| | G | 1.25 | 1.50 | |
| | H2 | 8 | 1.31 | |
| | L | 13.34 | 14.10 | |
| | L1 | 3.30 | 4.06 | |
| | L3 | 0.95 | 1.15 | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|--|-----|-----|-----------|------------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 100 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; I _D =0.25mA | 2.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =16A | | | 44 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} = 0V | | | ±0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =100V; V _{GS} = 0V;Tj=25°C V _{DS} =80V; V _{GS} = 0V;Tj=125°C | | | 25 250 | μ А |
| V _{SDF} | Diode forward voltage | I _{SD} =16A, V _{GS} = 0 V | | | 1.2 | V |



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